

Sheet 1 of 1								INFORMATION DISCLOSURE STATEMENT							
FORM PTO/SB/08 A&B (<i>modified</i>) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE LIST OF REFERENCES CITED BY APPLICANT(S) (<i>Use several sheets if necessary</i>) Date Submitted to PTO: March 22, 2011				ATTY DOCKET NO. 2003_1187A				SERIAL NO. 10/644,738							
				APPLICANT Tsuyoshi NAKAMURA et al.											
				FILING DATE August 21, 2003				GROUP 1795							
U.S. PATENT DOCUMENTS															
*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME			CLASS	SUBCLASS	FILING DATE IF APPROPRIATE						
	AA														
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FOREIGN PATENT DOCUMENTS															
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION								
						YES		NO							
	BA														
	BB														
	BC														
	BD														
	BE														
OTHER DOCUMENT(S) (<i>Including Author, Title, Date, Pertinent Pages, Etc.</i>)															
	CA	T. Kijima et al., "Low Temperature Deposition of Bi ₄ Ti ₃ O ₁₂ Thin Films by MOCVD", Functional Devices Lab. Sharp Corp., with "Concise Explanation of the Relevance with Respect to Extended Abstracts (The 42nd Spring Meeting, 1995); The Japan Society of Applied Physics and Related Societies", 29p-D-2.													
	CB	H. Watanabe et al., "Development of Y1 Materials (Bi Layer Structured Ferroelectrics) Thin-Film Capacitors (II)", Olympus Optical Co., Ltd. *Symetrix Co., with "Concise Explanation of the Relevance with Respect to Extended Abstracts (The 55th Autumn Meeting, 1994); The Japan Society of Applied Physics", 20p-M-19.													
	CC	Jun-Sung Chun et al., "Toward 0.1µm Contact Hole Process by Using Water Soluble Organic Over-Coating Material (WASOOM); Resist Flow Technique (III); Study on WASOOM, Top Flare and Etch Characterization", Advances in Resist Technology and Processing XVIII, Proceedings of SPIE, Vol. 4345 (2001), pages 647-654.													
	CD	S. Satoh et al., "Electrical Properties of Bi ₄ Ti ₃ O ₁₂ Thin Films by MOCVD", Functional Devices Lab. Sharp Corp., with "Concise Explanation of the Relevance with Respect to Extended Abstracts (The 42nd Spring Meeting, 1995); The Japan Society of Applied Physics and Related Societies", 29p-D-3.													
EXAMINER				/Christopher Young/ (04/25/2011)				DATE CONSIDERED				04/25/2011			

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /CY/

**Examiner: initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.*